

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	$20m\Omega$ @ $V_{GS} = 10V$	7.6A
30 V	$32m\Omega$ @ $V_{GS} = 4.5V$	6.0A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

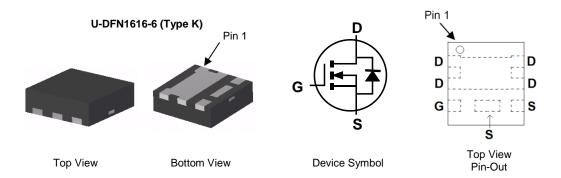
- Power Management Functions
- Loadswitch

Features and Benefits

- Typical Off-Board Profile of 0.6mm Ideally Suited for Thin Applications
- Low R_{DS(ON)} Minimizes Conduction Losses
- PCB Footprint of 2.56mm²
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: U-DFN1616-6 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper Leadframe).
- Terminals: Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.003 grams (Approximate)



Ordering Information (Note 4)

Product	Case	Packaging
DMT3020LFCL-7	U-DFN1616-6	3.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



20L = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020		2021
Code	С		D		Е		F	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$				7.6 6.0	А
Pulsed Drain Current (Note 7)		I _{DM}	40	Α	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	207	°C/W
Power Dissipation (Note 6)	PD	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	73	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 8)										
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$				
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1.0	μΑ	V _{DS} = 24V, V _{GS} = 0V				
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$				
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)									
Gate Threshold Voltage	V _{GS(TH)}	1	1.6	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$				
Static Drain-Source On-Resistance	7		15	20	mΩ	$V_{GS} = 10V, I_D = 9A$				
Static Drain-Source On-Resistance	R _{DS(ON)}	_	25	32	11177	$V_{GS} = 4.5V, I_D = 7A$				
Diode Forward Voltage	V _{SD}	_	0.78	1.0	V	V _{GS} = 0V, I _S = 2A				
DYNAMIC CHARACTERISTICS (Note 9)										
Input Capacitance	C _{ISS}	-	393	_	pF	T				
Output Capacitance	Coss		173	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz				
Reverse Transfer Capacitance	C _{RSS}	-	27	_	pF	1 = 1.0WH12				
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$				
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	7.0	_	nC					
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	3.6	_	nC	1, 45,4 6,				
Gate-Source Charge	Q _{GS}	_	0.9	_	nC	$V_{DS} = 15V, I_{D} = 9A$				
Gate-Drain Charge	Q_{GD}	_	1.5	_	nC	7				
Turn-On Delay Time	t _{D(ON)}	1	1.8	_	ns					
Turn-On Rise Time	t _R		1.9	_	ns	$V_{DD} = 15V, V_{GS} = 10V, I_D = 9A$				
Turn-Off Delay Time	t _{D(OFF)}		7.5	_	ns	$R_G = 6\Omega$				
Turn-Off Fall Time	t _F		2.4	_	ns					
Body Diode Reverse Recovery Time	t _{RR}	_	10	_	ns	I _F = 9A, dI/dt = 100A/µs				
Body Diode Reverse Recovery Charge	Q _{RR}		2.6	_	nC	11 = 9A, αι/αι = 100A/μS				

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

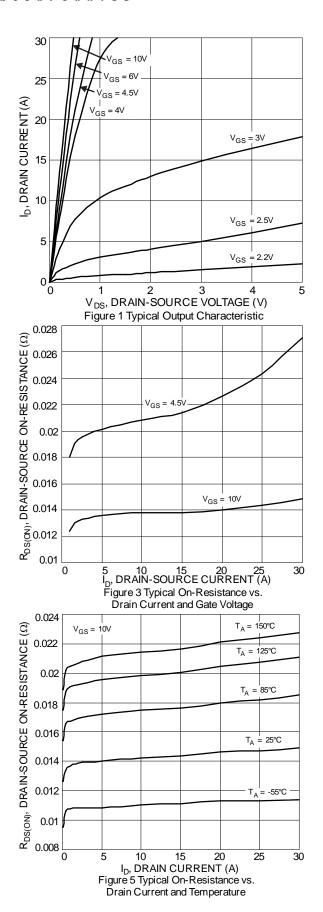
^{7.} Repetitive rating, pulse width limited by junction temperature.

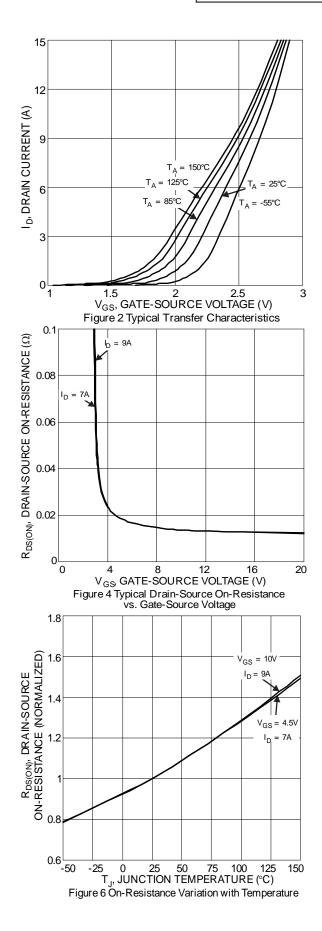
^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.

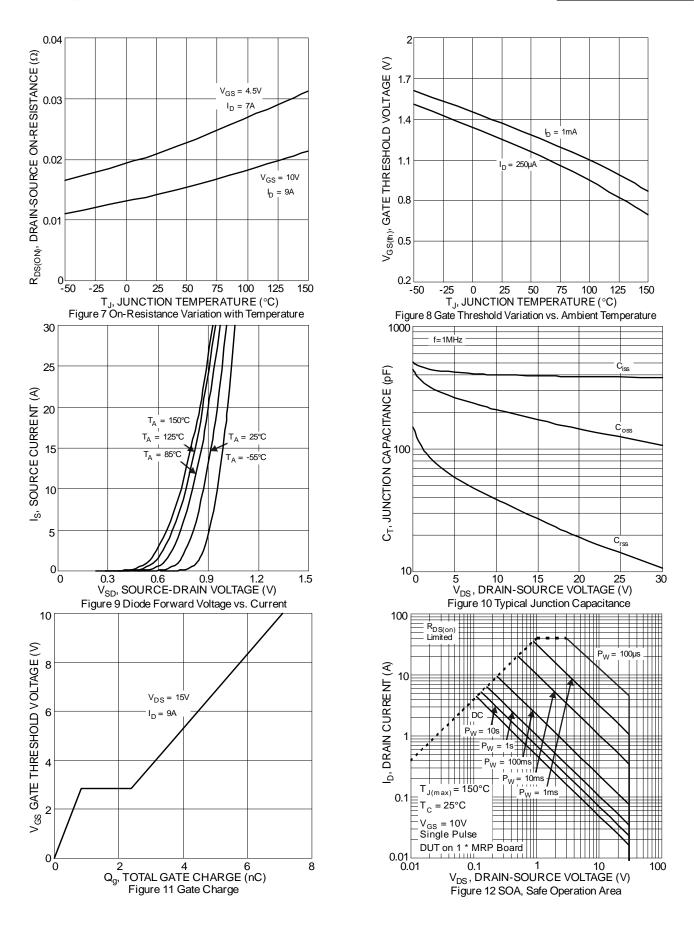
^{10.} IAS and EAS rating are based on low frequency and duty cycles to keep $T_J = +25$ °C.



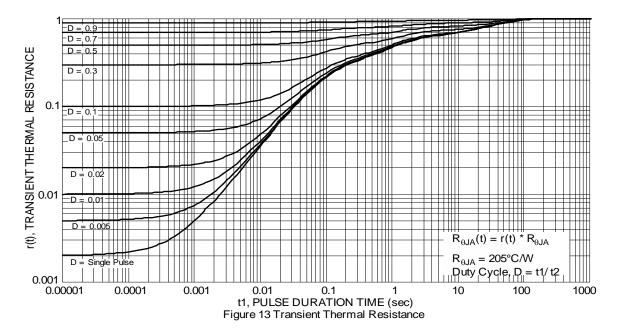










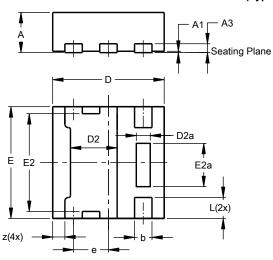




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

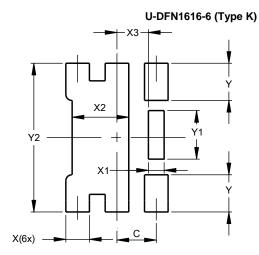
U-DFN1616-6 (Type K)



U-DFN1616-6 (Type K)							
Dim	Min Max Typ						
Α	0.55	0.60	0.575				
A1	0.00	0.05	0.02				
A3	-	_	0.13				
b	0.20	0.30	0.25				
D	1.55	1.65	1.60				
D2	0.57	0.77	0.67				
D2a	0.10	0.30	0.20				
е	ı	-	0.50				
Е	1.55	1.65	1.60				
E2	1.30	1.50	1.40				
E2a	0.52	0.72	0.62				
٦	0.25	0.35	0.30				
Z	1	_	0.175				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value			
Dilliensions	(in mm)			
С	0.500			
X	0.300			
X1	0.200			
X2	0.720			
Х3	0.400			
Y	0.475			
Y1	0.620			
٧2	1 000			

July 2016 © Diodes Incorporated



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